COMPLEMENTARY PAIR SMALL SIGNAL TRANSISTOR IN SOT363

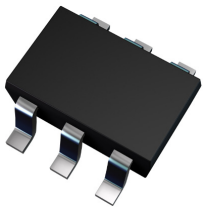
Features

- Epitaxial Die Construction
- Two Internally Isolated NPN/PNP Transistors in One Package
  NPN = 4401
  PNP = 4403
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

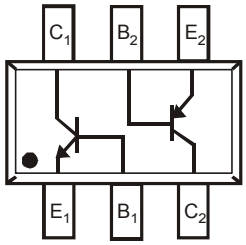
Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Finish. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.006 grams (approximate)

SOT363



Top View



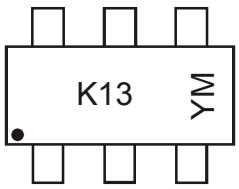
Device Schematic
Top View

Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
MMDT4413-7-F	K13	7	8	3,000

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated’s definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



K13= Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: A = 2013)
M = Month (ex: 9 = September)

Date Code Key

Year	2010	2011	2012	2013	2014	2015	2016	2017
Code	X	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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Absolute Maximum Ratings: NPN, 4401 Type (Q_1) (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	600	mA

Absolute Maximum Ratings: PNP, 4403 Type (Q_2) (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-600	mA

Thermal Characteristics – Total Device (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5) Total Device	P_D	200	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	625	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +150	°C

Note: 5. For a device mounted on minimum recommended pad layout with 1oz copper that is on a single-sided 1.6mm FR4 PCB; the device is measured under still air conditions whilst operating in a steady-state.

Thermal Characteristics – Total Device

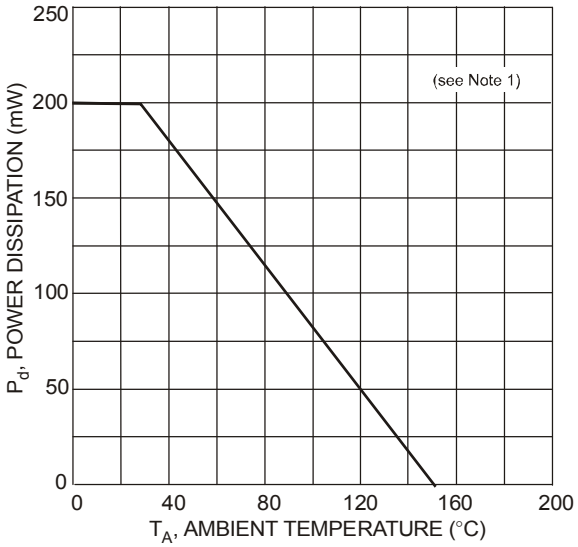

Fig. 1, Power Derating Curve (Total Device)

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Electrical Characteristics, NPN 4401 Section (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)					
Collector-Base Breakdown Voltage	BV_{CBO}	60	—	V	I_C = 100μA, I_E = 0
Collector-Emitter Breakdown Voltage	BV_{CEO}	40	—	V	I_C = 1.0mA, I_B = 0
Emitter-Base Breakdown Voltage	BV_{EBO}	6.0	—	V	I_E = 100 μA, I_C = 0
Collector Cutoff Current	I_{CEX}	—	100	nA	V_{CE} = 35V, $V_{EB(OFF)}$ = 0.4V
Base Cutoff Current	I_{BL}	—	100	nA	V_{CE} = 35V, $V_{EB(OFF)}$ = 0.4V
ON CHARACTERISTICS (Note 6)					
DC Current Gain	h_{FE}	20 40 80 100 40	— — — 300 —	—	I_C = 100μA, V_{CE} = 1.0V I_C = 1.0mA, V_{CE} = 1.0V I_C = 10mA, V_{CE} = 1.0V I_C = 150mA, V_{CE} = 1.0V I_C = 500mA, V_{CE} = 2.0V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.40 0.75	V	I_C = 150mA, I_B = 15mA I_C = 500mA, I_B = 50mA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	0.75 —	0.95 1.2	V	I_C = 150mA, I_B = 15mA I_C = 500mA, I_B = 50mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{cb}	—	6.5	pF	V_{CB} = 5.0V, f = 1.0MHz, I_E = 0
Input Capacitance	C_{eb}	—	30	pF	V_{EB} = 0.5V, f = 1.0MHz, I_C = 0
Input Impedance	h_{ie}	1.0	15	kΩ	V_{CE} = 10V, I_C = 1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h_{re}	0.1	8.0	x 10^{-4}	
Small Signal Current Gain	h_{fe}	40	500	—	
Output Admittance	h_{oe}	1.0	30	μS	
Current Gain-Bandwidth Product	f_T	250	—	MHz	V_{CE} = 10V, I_C = 20mA, f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t_d	—	15	ns	V_{CC} = 30V, I_C = 150mA, $V_{BE(off)}$ = 2.0V, I_{B1} = 15mA
Rise Time	t_r	—	20	ns	
Storage Time	t_s	—	225	ns	V_{CC} = 30V, I_C = 150mA, I_{B1} = I_{B2} = 15mA
Fall Time	t_f	—	30	ns	

Note: 6. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%

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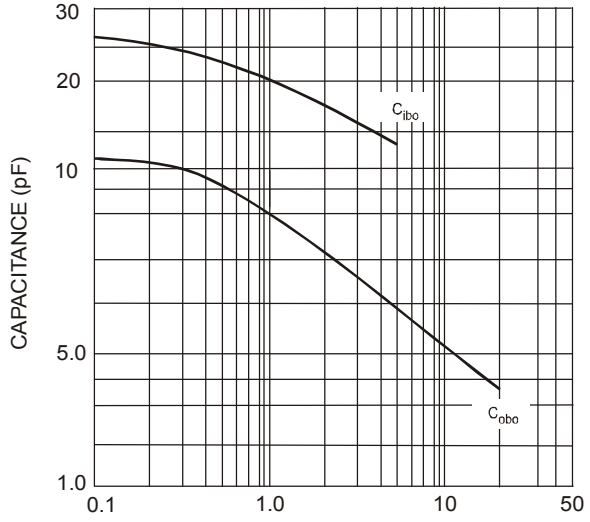

Fig. 1 Typical Capacitance (4401)

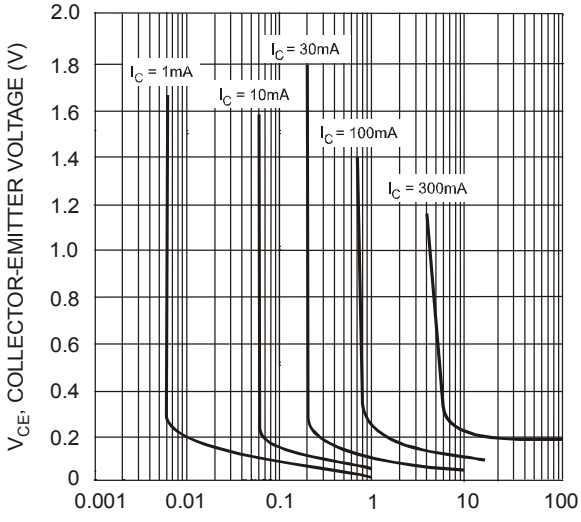

Fig. 2 Typical Collector Saturation Region (4401)

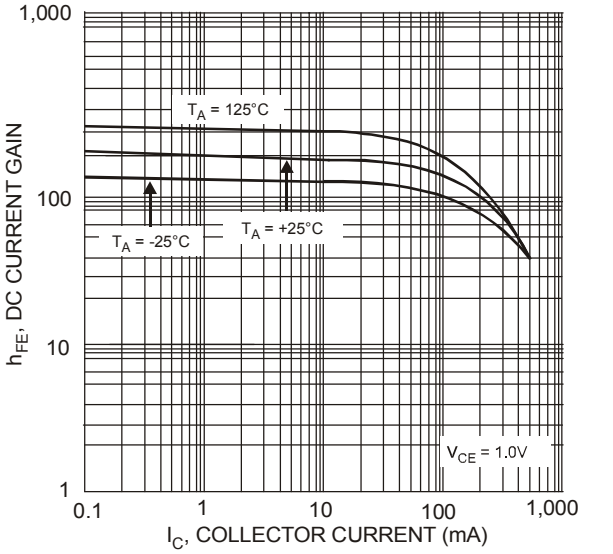

Fig. 3 Typical DC Current Gain vs. Collector Current (4401)

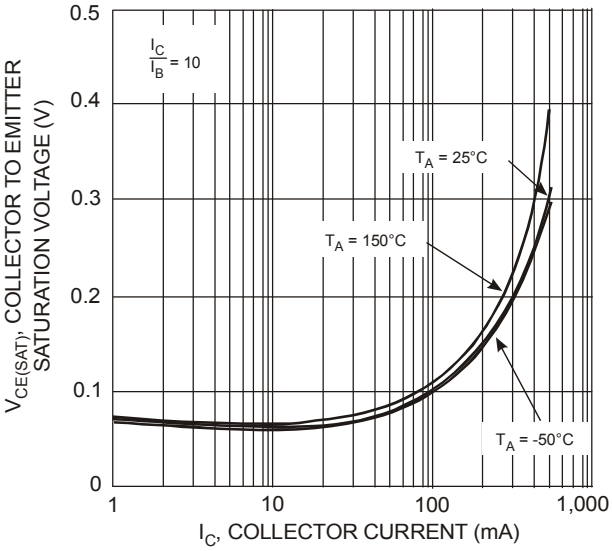

Fig. 4 Collector Emitter Saturation Voltage vs. Collector Current (4401)

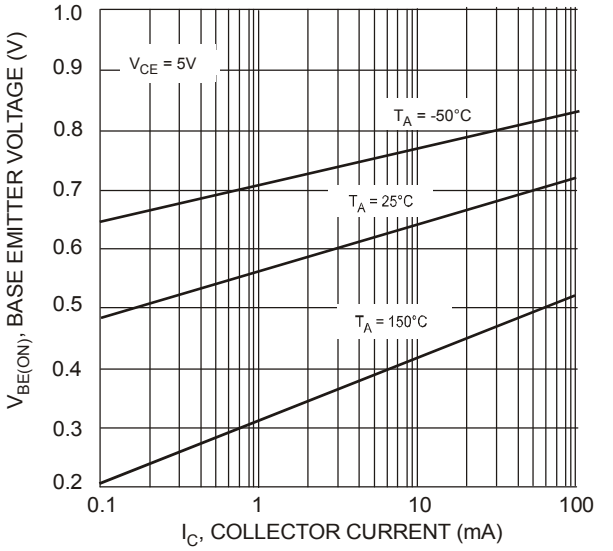

Fig. 5 Base Emitter Voltage vs. Collector Current (4401)

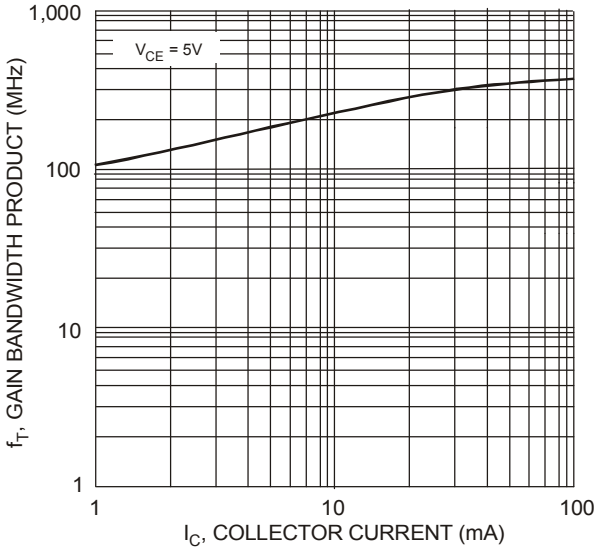

Fig. 6 Gain Bandwidth Product vs. Collector Current (4401)

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Electrical Characteristics, PNP 4403 Section (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)					
Collector-Base Breakdown Voltage	BV_{CBO}	-40	—	V	I_C = -100µA, I_E = 0
Collector-Emitter Breakdown Voltage	BV_{CEO}	-40	—	V	I_C = -1.0mA, I_B = 0
Emitter-Base Breakdown Voltage	BV_{EBO}	-5.0	—	V	I_E = -100µA, I_C = 0
Collector Cutoff Current	I_{CEX}	—	-100	nA	V_{CE} = -35V, $V_{EB(OFF)}$ = -0.4V
Base Cutoff Current	I_{BL}	—	-100	nA	V_{CE} = -35V, $V_{EB(OFF)}$ = -0.4V
ON CHARACTERISTICS (Note 6)					
DC Current Gain	h_{FE}	30 60 100 100 20	— — — 300 —	—	I_C = -100µA, V_{CE} = -1.0V I_C = -1.0mA, V_{CE} = -1.0V I_C = -10mA, V_{CE} = -1.0V I_C = -150mA, V_{CE} = -2.0V I_C = -500mA, V_{CE} = -2.0V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	-0.40 -0.75	V	I_C = -150mA, I_B = -15mA I_C = -500mA, I_B = -50mA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	-0.75 —	-0.95 -1.30	V	I_C = -150mA, I_B = -15mA I_C = -500mA, I_B = -50mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{cb}	—	8.5	pF	V_{CB} = -10V, f = 1.0MHz, I_E = 0
Input Capacitance	C_{eb}	—	30	pF	V_{EB} = -0.5V, f = 1.0MHz, I_C = 0
Input Impedance	h_{ie}	1.5	15	kΩ	V_{CE} = -10V, I_C = -1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h_{re}	0.1	8.0	x 10^{-4}	
Small Signal Current Gain	h_{fe}	60	500	—	
Output Admittance	h_{oe}	1.0	100	µS	
Current Gain-Bandwidth Product	f_T	200	—	MHz	V_{CE} = -10V, I_C = -20mA, f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t_d	—	15	ns	V_{CC} = -30V, I_C = -150mA, $V_{BE(off)}$ = -2.0V, I_{B1} = -15mA
Rise Time	t_r	—	20	ns	
Storage Time	t_s	—	225	ns	V_{CC} = -30V, I_C = -150mA, I_{B1} = I_{B2} = -15mA
Fall Time	t_f	—	30	ns	

Note: 6. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%

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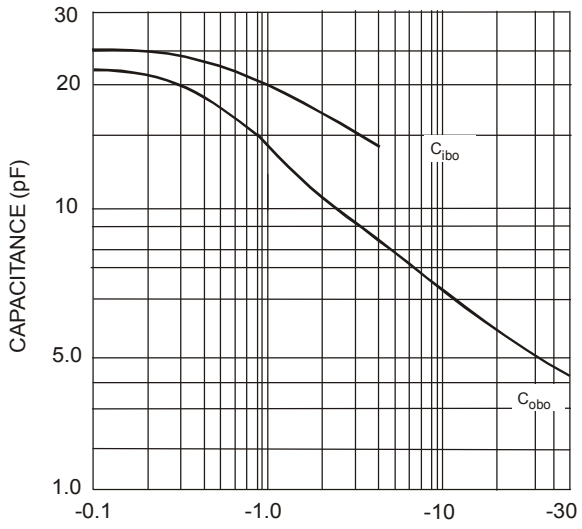

Fig. 7 Typical Capacitance (4403)

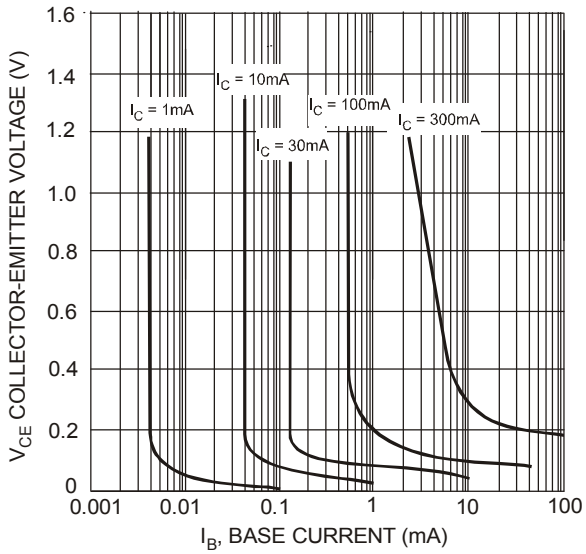

Fig. 8 Typical Collector Saturation Region (4403)

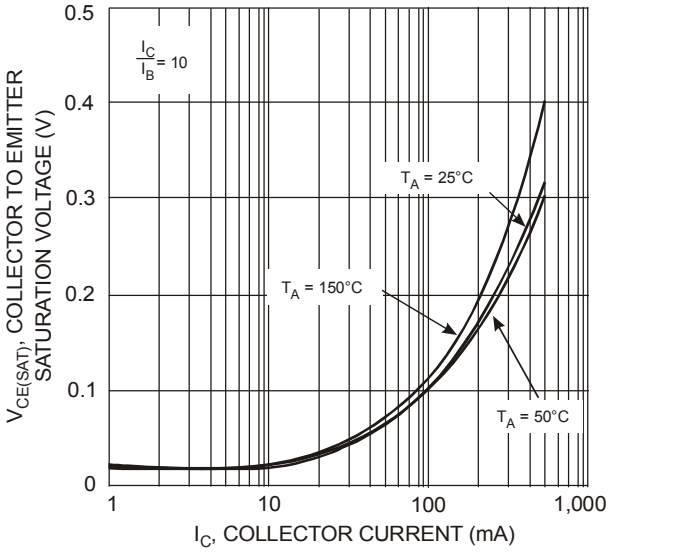

Fig. 9 Collector Emitter Saturation Voltage vs. Collector Current (4403)

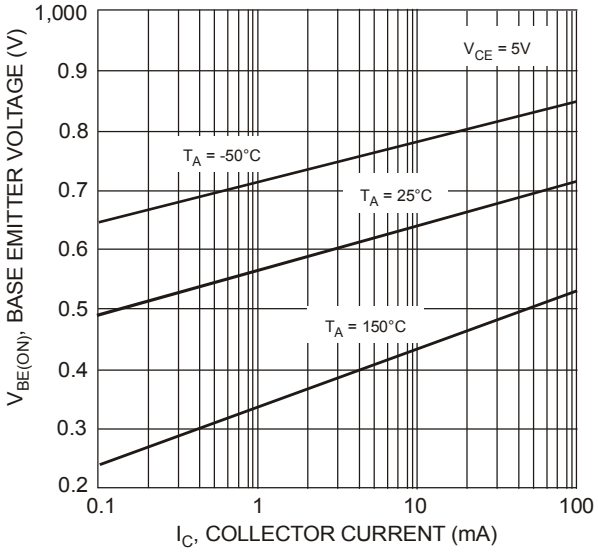

Fig. 10 Base-Emitter Voltage vs. Collector Current (4403)

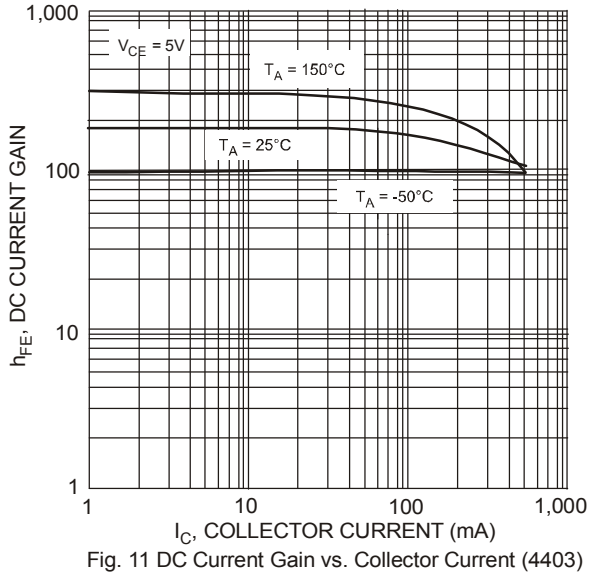

Fig. 11 DC Current Gain vs. Collector Current (4403)

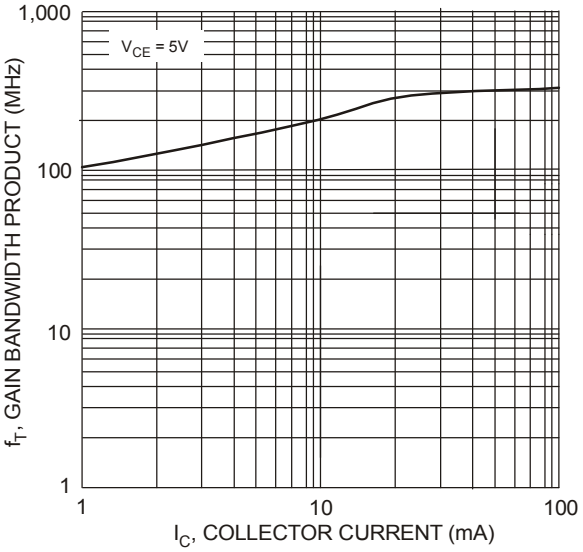

Fig. 12 Gain Bandwidth Product vs. Collector Current (4403)

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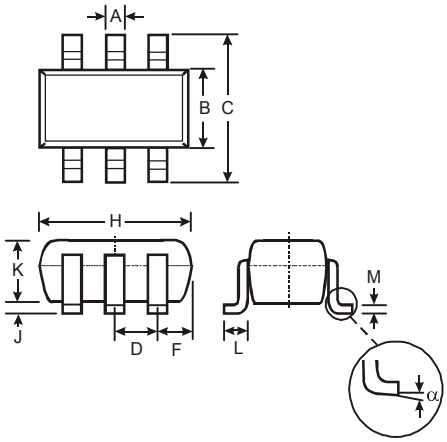
Package Outline Dimensions

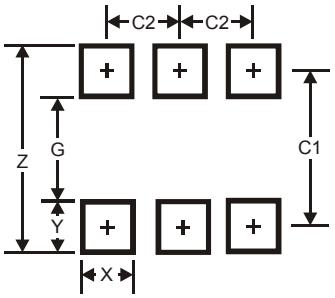
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT363			
Dim	**Min**	**Max**	**Typ**
A	0.10	0.30	0.25
B	1.15	1.35	1.30
C	2.00	2.20	2.10
D	0.65 Typ		
F	0.40	0.45	0.425
H	1.80	2.20	2.15
J	0	0.10	0.05
K	0.90	1.00	1.00
L	0.25	0.40	0.30
M	0.10	0.22	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C1	1.9
C2	0.65

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2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

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